Product data sheet

1. General description

EEPP[™]- Efficiency Enhanced Pt Planar rectifier in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · Fast switching
- · Reduces switching losses with improved lower reverse recovery charge
- Soft recovery characteristics
- Low thermal resistance
- Low leakage current
- Planar termination structure
- High operating temperature capability (T_{i (max)} = 175°C)
- Higher I_{FSM} capability

3. Applications

- · Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

4. Quick reference data

Table 1. Quick reference data

lues		Unit					
	Values						
1200		V					
15		А					
30		А					
180		А					
200		Α					
Тур	Max	Unit					
Static characteristics							
2.5	3.2	V					
2.0	-	V					
45	-	ns					
•	•						
-	-	mJ					
1	15 80 80 00 Typ 2.5 2.0	15 30 80 00 Typ Max 2.5 3.2 2.0 -					

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	А	anode	}	001aaa020
mb	mb	mounting base; connected to cathod	1 2 TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYC15-1200P		Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC15-1200P	BYC15-1200P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		1200	V
V_{RWM}	crest working reverse voltage		1200	V
V_R	reverse voltage	DC	1200	V
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 120$ °C; Fig. 1; Fig. 2; Fig. 3	15	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 120 °C; square-wave pulse	30	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	180	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	200	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C

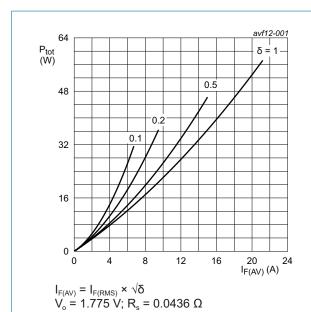
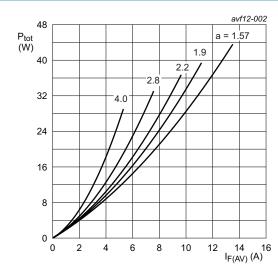
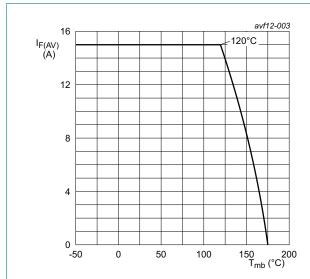


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ Vo = 1.775 V; Rs = 0.0436 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





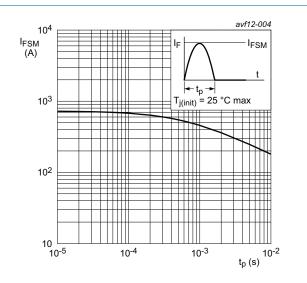
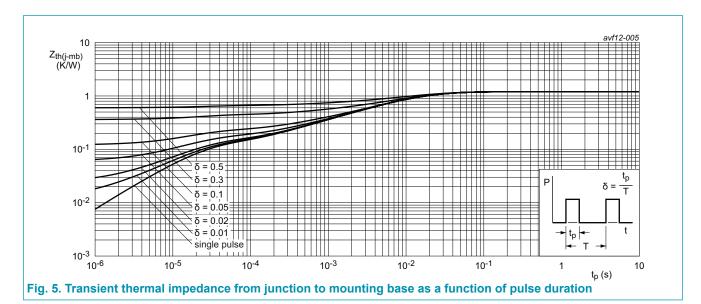


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 5	-	-	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



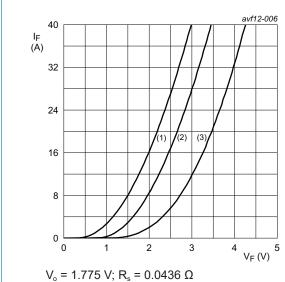
10. Characteristics

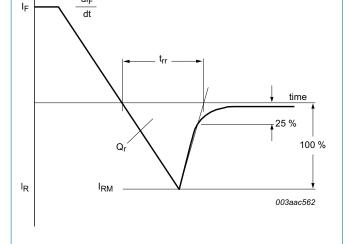
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _F	forward current	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.2	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	2.0	-	V
I _R	reverse current	V _R = 1200 V; T _j = 25 °C	-	-	100	μΑ
		V _R = 1200 V; T _j = 150 °C	-	-	500	μA
Dynamic	characteristics					
Q _r	reverse charge	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	394	-	nC
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	1003	-	nC
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	1143	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	45	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	61	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	120	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	128	-	ns
I _{RM}	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	12.6	-	А
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	16.7	-	А
		I _F = 15 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 150 °C; <u>Fig. 7</u>	-	17.8	-	А
Avalanci	ne energy					
E _{AS}	non-repetitive avalanche energy	T _{j(init)} = 25 °C	20	-	-	mJ

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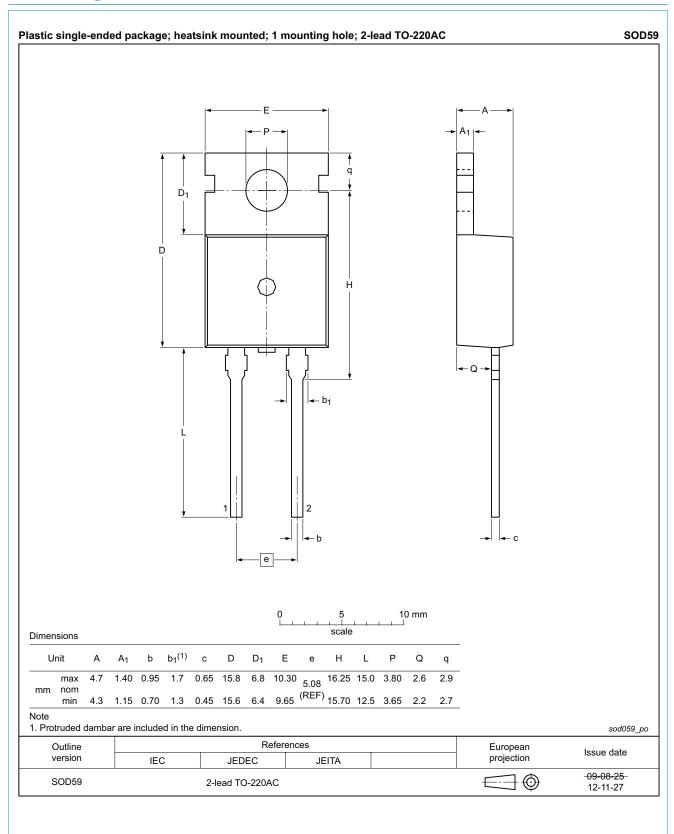
 dI_F

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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13. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10	Characteristics	6
11	. Package outline	8
	Legal information	
	3. Contents	

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